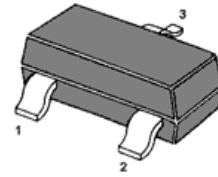


# BCV26 / BCV46

## PNP Silicon Epitaxial Planar Darling Transistors

### Applications

- For preamplifier input applications



1.Base 2.Emitter 3.Collector  
SOT-23 Plastic Package

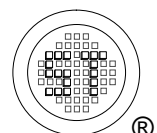
### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	BCV26 BCV46 $-V_{\text{CBO}}$	40 80	V
Collector Emitter Voltage	BCV26 BCV46 $-V_{\text{CEO}}$	30 60	V
Emitter Base Voltage	$-V_{\text{EBO}}$	10	V
Collector Current	$-I_{\text{C}}$	500	mA
Peak Collector Current	$-I_{\text{CM}}$	800	mA
Base Current	$-I_{\text{B}}$	100	mA
Total Power Dissipation	$P_{\text{tot}}$	200	mW
Junction Temperature	$T_{\text{j}}$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{\text{stg}}$	- 65 to + 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient <sup>1)</sup>	$R_{\theta\text{JA}}$	625	$^\circ\text{C/W}$

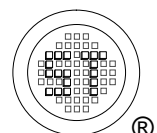
<sup>1)</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout



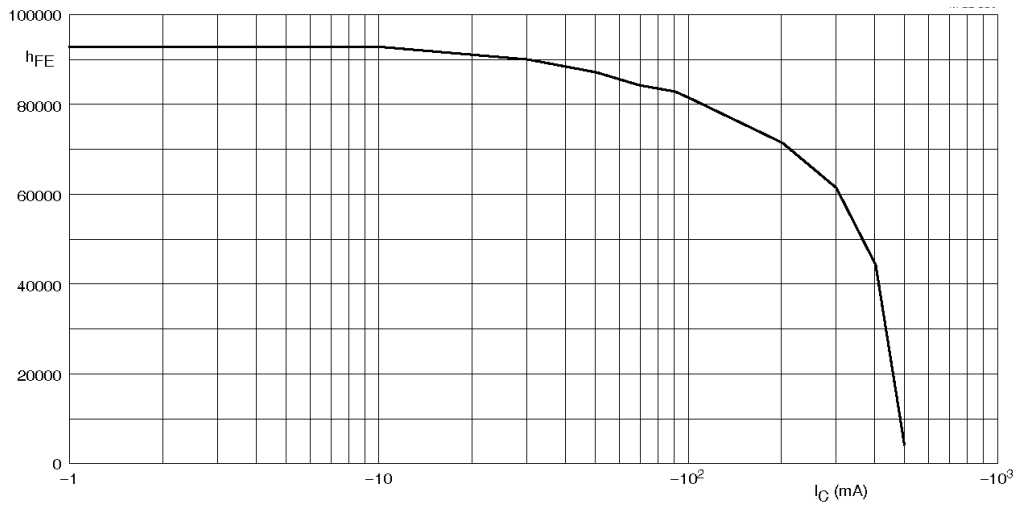
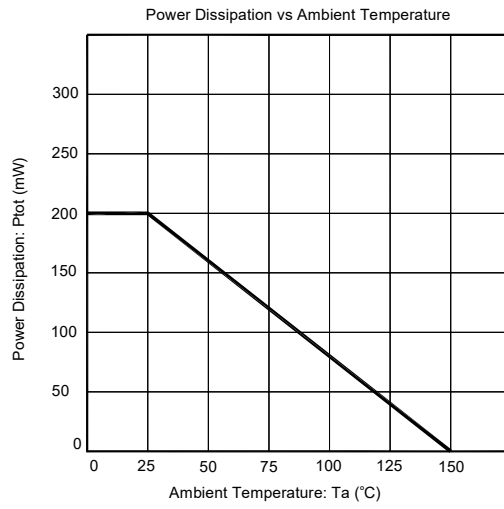
## BCV26 / BCV46

### Characteristics at Ta = 25°C

Parameter		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$ , $-I_C = 1\text{ mA}$  at $-V_{CE} = 5\text{ V}$ , $-I_C = 10\text{ mA}$  at $-V_{CE} = 5\text{ V}$ , $-I_C = 100\text{ mA}$	BCV26	$h_{FE}$	4000	-	-	-
	BCV46	$h_{FE}$	2000	-	-	-
	BCV26	$h_{FE}$	10000	-	-	-
	BCV46	$h_{FE}$	4000	-	-	-
	BCV26	$h_{FE}$	20000	-	-	-
	BCV46	$h_{FE}$	10000	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$ at $-V_{CB} = 60\text{ V}$	BCV26	$-I_{CBO}$	-	-	100	nA
	BCV46		-	-	100	
Emitter Base Cutoff Current at $-V_{EB} = 10\text{ V}$		$-I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	BCV26	$-V_{(BR)CBO}$	40	-	-	V
	BCV46		80	-	-	
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	BCV26	$-V_{(BR)CEO}$	30	-	-	V
	BCV46		60	-	-	
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$		$-V_{(BR)EBO}$	10	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$ , $-I_B = 0.1\text{ mA}$		$-V_{CE(sat)}$	-	-	1	V
Base Emitter Saturation Voltage at $-I_C = 100\text{ mA}$ , $-I_B = 0.1\text{ mA}$		$-V_{BE(sat)}$	-	-	1.5	V
Base Emitter On-state Voltage at $-I_C = 10\text{ mA}$ , $-V_{CE} = 5\text{ V}$		$-V_{BE(on)}$	-	-	1.4	V
Transition Frequency at $-V_{CE} = 5\text{ V}$ , $-I_C = 30\text{ mA}$ , $f = 100\text{ MHz}$		$f_T$	-	220	-	MHz

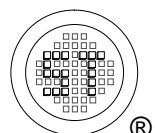


## Electrical Characteristics Curves



$V_{CE} = -2V.$

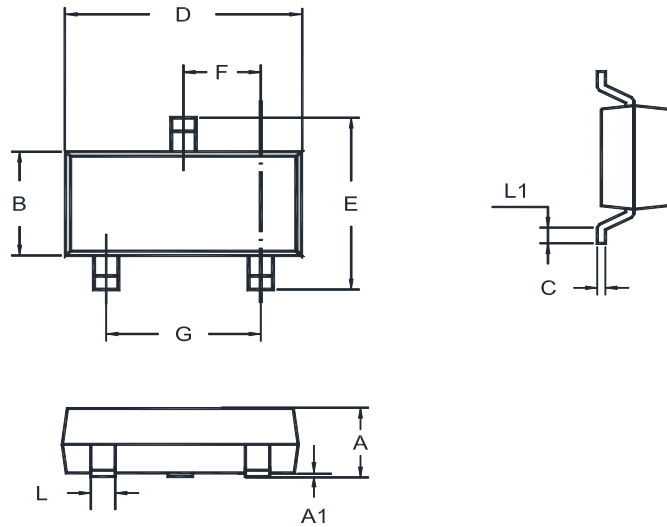
Fig.2 DC current gain; typical values.



# BCV26 / BCV46

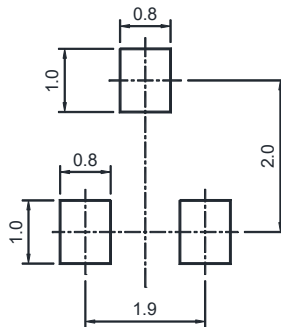
## Package Outline (Dimensions in mm)

SOT-23



Unit	A	A1	B	C	D	E	F	G	L	L1
mm	1.20	0.100	1.40	0.19	3.04	2.6	1.02	2.04	0.51	0.2
	0.89	0.013	1.20	0.08	2.80	2.2	0.89	1.78	0.37	MIN

## Recommended Soldering Footprint



## Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

## Marking information

- "XK" = Part No.
- "YM" = Date Code Marking
- "Y" = Year
- "M" = Month

Font type: Arial

